

IR Laser Diode

Application

Industrial use / Biomedical

Property

Wavelength $\lambda = 780 \text{ nm}$

Output Power = 100 mW

Package Type = $\phi 5.6 \text{ mm}$

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer.

Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

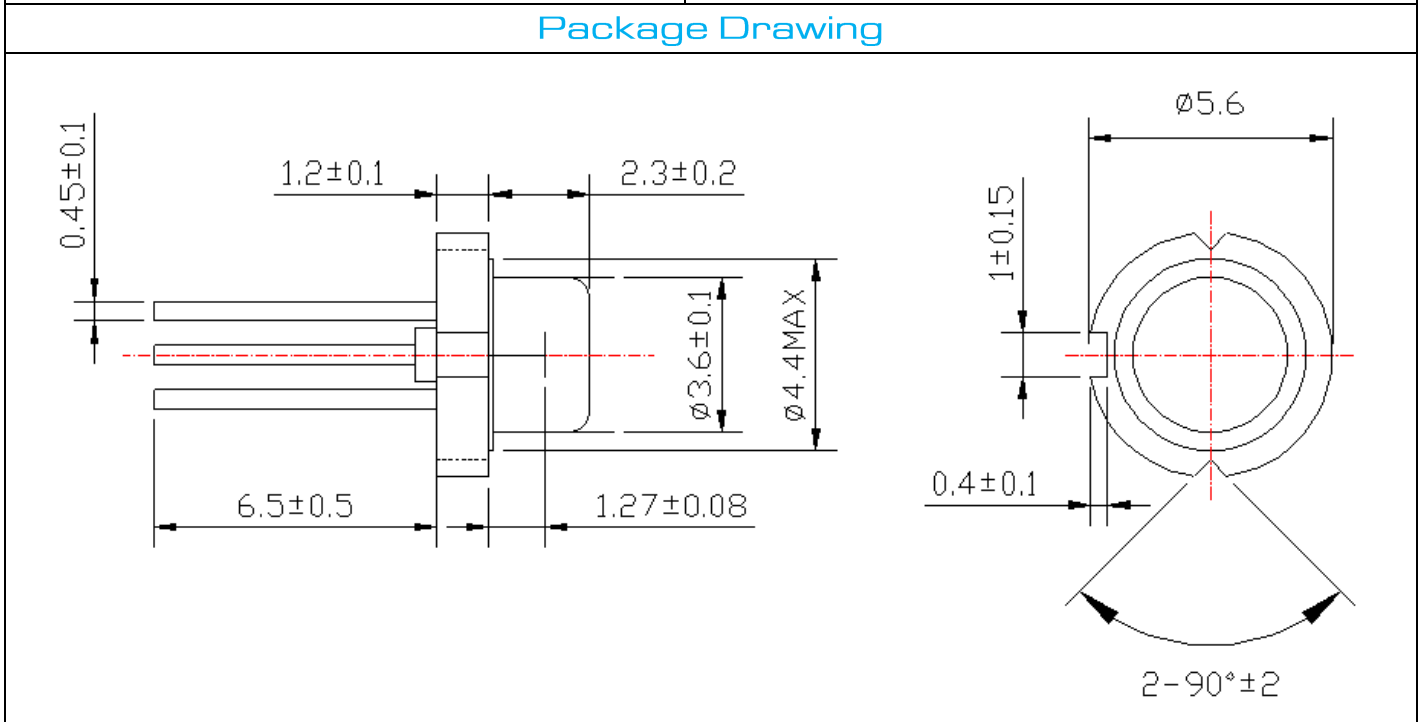
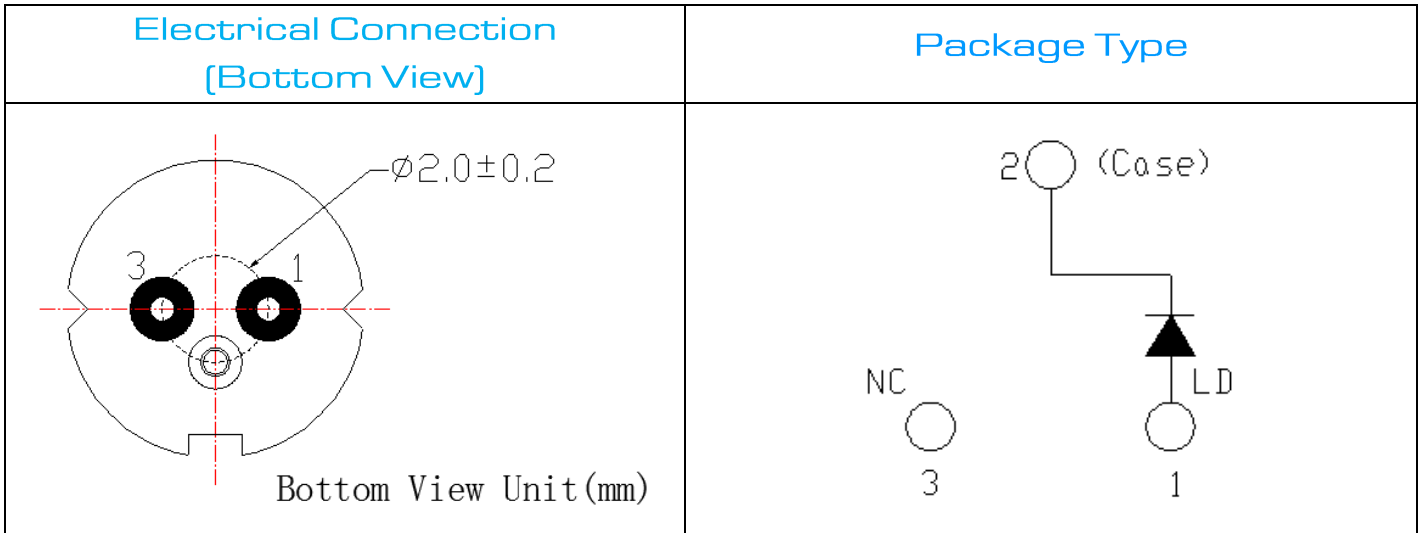


IR Laser Diode Key features

Absolute Maximum Rating at Tc=25°C			
Items	Symbols	Values	Unit
Optical Output Power	Po(CW)	110	mW
	Po(Push)	250	mW
Laser Reverse Voltage	V	2	V
Operating Temperature	To	-10~+70	°C
Storage Temperature	Ts	-40~+85	°C

Electrical and Optical Characteristics at Tc=25°C						
Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	I_{th}	-	55	70	mA	-
Operating Current	I_{op}	-	150	165	mA	Po=100 mW
Operating Voltage	V_{op}	-	2.0	2.3	V	Po=100 mW
Slope Efficiency	η	-	0.8	1.0	-	mW/mA

Peak Wavelength	λ_p	775	780	795	nm	Po=100 mW
Beam Divergence (FWHM)	$\theta_{//}$	8	10	12	deg	Po=100 mW
	θ_{\perp}	16	22	22	deg	Po=100 mW



Specifications are subject to change without notice.

